2048 BIT BIPOLAR TTL

PROGRAMMABLE READ ONLY MEMORY
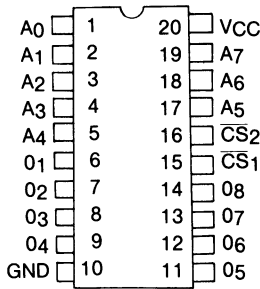
Description

The μPB421C and μPB421D are high speed, electrically programmable, fully decoded 2048 bit TTL read only memories. On-chip address decoding, two chip select inputs and three-state outputs allow easy expansion of memory capability. The μPB421C and μPB421D are fabricated with logic level zero (low); logic level one High) can be electrically programmed into the selected bit locations. The same address inputs are used for both programming and reading.

Features

- 256 WORDS x 8 BITS organization (Fully decoded)
- TTL Interface
- Fast read access time   : 40 ns MAX. (μPB421–1)
- Medium power consumption   : 500 mW TYP.
- Two chip select inputs for memory expansion
- Three-state outputs
- Cerdip 20-Lead Dual In-Line Package (μPB421D)
- Plastic 20-Lead Dual In-Line Package (μPB421C)
- Fast programming time   : 200 μs/bit TYP.
- Compatibility with   : MMI's 6309 and equivalent devices (as a ROM)

Connection Diagram (Top View)

A0	1	20 VCC
A1	2	19 A7
A2	3	18 A6
A3	4	17 A5
A4	5	16 $\overline{CS}_2$
0₁	6	15 $\overline{CS}_1$
0₂	7	14 0₈
0₃	8	13 0₇
0₄	9	12 0₆
GND	10	11 0₅

A0 to A7 : Address Inputs
0₁ to 0₈ : Data Outputs
$\overline{CS}_1$, $\overline{CS}_2$: Chip Select Inputs (Active Low)
VCC : Power Supply (+5V)
GND : Ground

Operation

1. Programming

A logic one can be permanently programmed into a selected bit location by using special equipment (programmer). First, the desired word is selected by the eight address inputs in TTL levels. Either or both of the Chip Select inputs should be at a logical one. Secondly, a train of high current programming pulses is applied to the desired output. After the sensed voltage indicates that the selected bit is in the logic one state, an additional pulse train is applied, then is stopped.

2. Reading

To read the memory, both of the two Chip Select inputs must be held at a logical zero. The outputs then correspond to the data programmed in the selected words. When either or both of the two Chip Select inputs are at a logical one, all the outputs will be high (floating).

Logic Diagram
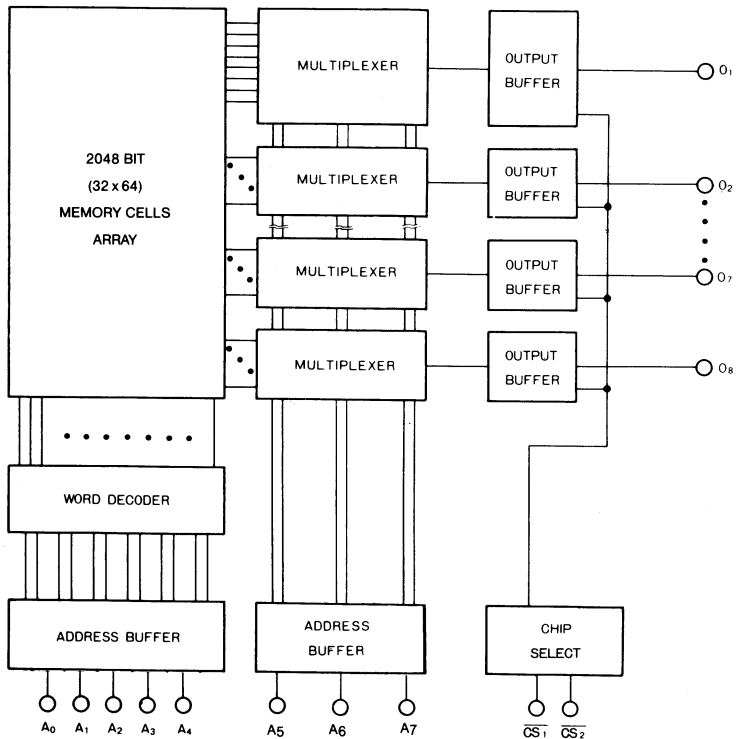
ABSOLUTE MAXIMUM RATINGS

Supply Voltage	V_{CC}	-0.5 to $+7.0$	V
Input Voltage	V_I	-0.5 to $+5.5$	V
Output Voltage	V_O	-0.5 to $+5.5$	V
Output Current	I_O	50	mA
Operating Temperature	T_{opt}	-25 to $+75$	°C
Storage Temperature (Cerdip Package)	T_{stg}	-65 to $+150$	°C
Storage Temperature (Plastic Package)	T_{stg}	-55 to $+125$	°C

D.C. CHARACTERISTICS ($V_{CC}=4.5$ to 5.5 V, $T_a=0$ to $+75$ °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Input High Voltage	V_{IH}	2.0			V		
Input Low Voltage	V_{IL}			0.85	V		
Input High Current	I_{IH}			40	μA	$V_I=5.5$ V	$V_{CC}=5.5$ V
Input Low Current	$-I_{IL}$			0.25	mA	$V_I=0.4$ V	$V_{CC}=5.5$ V
Output Low Voltage	V_{OL}			0.45	V	$I_O=16$ mA	$V_{CC}=4.5$ V
Output Leakage Current	I_{OFF1}			40	μA	$V_O=5.5$ V	$V_{CC}=5.5$ V
Output Leakage Current	$-I_{OFF2}$			40	μA	$V_O=0.4$ V	$V_{CC}=5.5$ V
Input Clamp Voltage	$-V_{IC}$			1.2	V	$I_I=-18$ mA	$V_{CC}=4.5$ V
Power Supply Current	I_{CC}		90	140	mA	All Inputs Grounded.	$V_{CC}=5.5$ V
Output High Voltage	V_{OH}	2.4			V	$I_O=-2.4$ mA	$V_{CC}=4.5$ V
Output Short Circuit Current	$-I_{SC}$	15		60	mA	$V_O=0$ V	

CAPACITANCE ($V_{CC}=5$ V, $f=1$ MHz, $T_a=25$ °C)

CHARACTERISTIC	SYMBOL	MIN.	MAX.	UNIT	TEST CONDITIONS
Input Capacitance	C_{IN}		8	pF	$V_{IN}=2.5$ V
Output Capacitance	C_{OUT}		10	pF	$V_{OUT}=2.5$ V

A.C. CHARACTERISTICS ($V_{CC}=4.5$ to 5.5 V, $T_a=0$ to $+75$°C)

Characteristic	Symbol	μPB421C/D-1		μPB421C/D		Unit
		min.	max.	min.	max.	
Address Access Time	t_{AA}		40		50	ns
Chip Select Access Time	t_{ACS}		30		30	ns
Chip Select Disable Time	t_{DCS}		30		30	ns

Note 1. Output Load: See Fig. 1.
Note 2. Input Waveform: 0.0 V for low level and 3.0 V for high level, less than 10 ns for both rise and fall times.
Note 3. Measurement References: 1.5 V for both inputs and outputs.
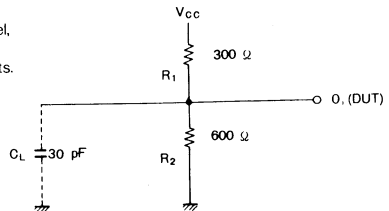Note 4. C_L in Fig. 1 includes jig and probe stray capacitances.

Fig. 1

Programming Specification

It is imperative that this specification be rigorously observed in order to correctly program the μPB421C and μPB421D. NEC will not accept responsibilty for any device found to be defective if it were not programmed according to this specification.

CHARACTERISTIC.	LIMIT	UNIT	NOTES
Ambient Temperature	25 ± 5	°C	
Programming Pulse			
Amplitude	200 ± 5 %	mA	
Clamp Voltage	28 + 0 % − 2 %	V	
Ramp Rate (Both in Rise and in Fall)	70 MAX.	V / μs	
Pulse Width	7.5 ± 5 %	μs	15 V point/150 Ω load
Duty Cycle	70 % MIN.		
Sense Current			
Amplitude	20 ± 0.5	mA	
Clamp Voltage	28 + 0 % − 2 %	V	
Ramp Rate	70 MAX.	V / μs	15 V point/150 Ω load
Sense Current Interruption before and after address change	10 MIN.	μs	
Programming V_{CC}	5.0 + 5 % − 0 %	V	
Maximum Sensed Voltage * for programmed "1"	7.0 ± 0.1	V	
Delay from trailing edge of programming pulse before sensing output voltage	0.7 MIN.	μs	

* A bit is judged to be programmed when two successive sense readings 10 μs apart with no intervening programming pulse, pass the limit.   When this condition has been met, four additional pulses are applied and the pulse train, then the sense current is terminated.
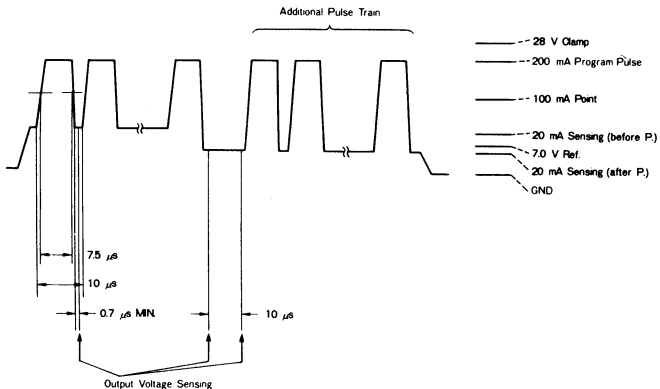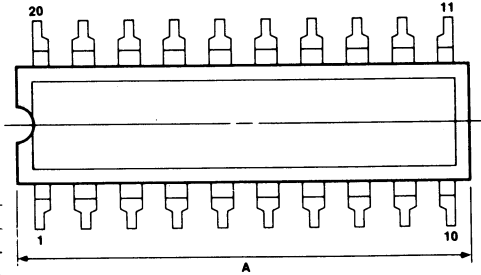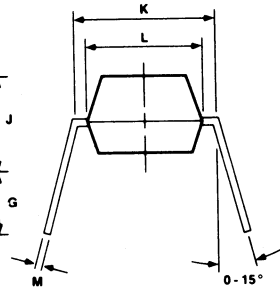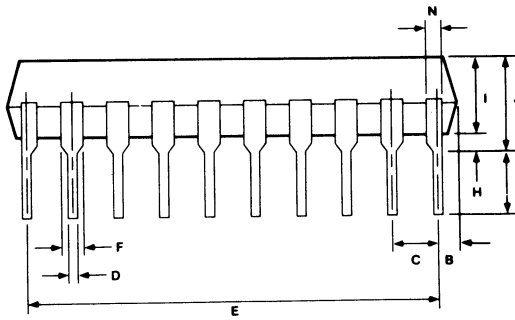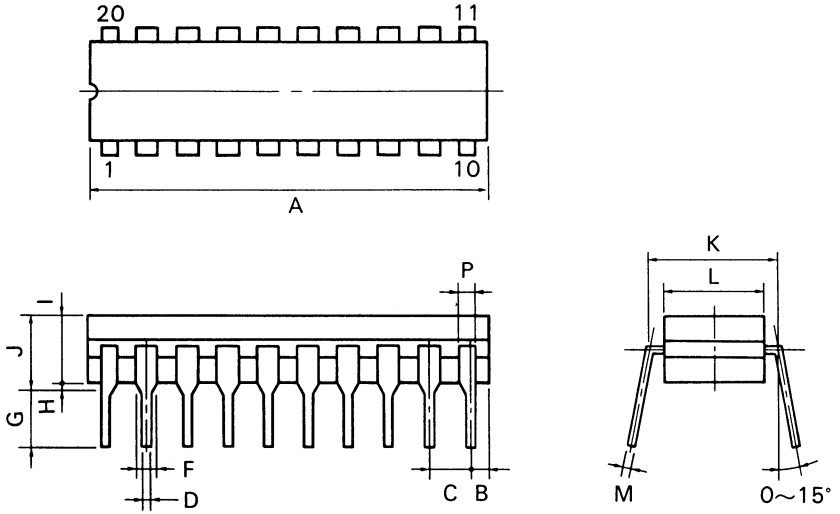

Fig. 2 Typical Output Voltage Waveform.

Package Dimensions

20PIN Plastic DIP

Item	Millimeters
A	25.40 max
B	1.27 max
C	2.54 [TP]
D	.50 ± .10
E	22.86
F	1.1 min
G	3.5 ± .30
H	.51 min
I	4.31 max
J	5.08 max
K	7.62 [TP]
L	6.4
M	.25 $^{+.10}_{-.05}$
N	.9 min

Package Dimensions
20 PIN Cerdip (300mil)

ITEM	MILLIMETERS
A	25.40 MAX.
B	1.27 MAX.
C	2.54 (T.P.)
D	$0.46^{\pm0.05}$
F	1.42 MIN.
G	$3.5^{\pm0.3}$
H	0.51 MIN.
I	3.95
J	5.08 MAX.
K	7.62 (T.P.)
L	7.32
M	$0.25^{\pm0.06}$
N	0.25
P	0.89 MIN.